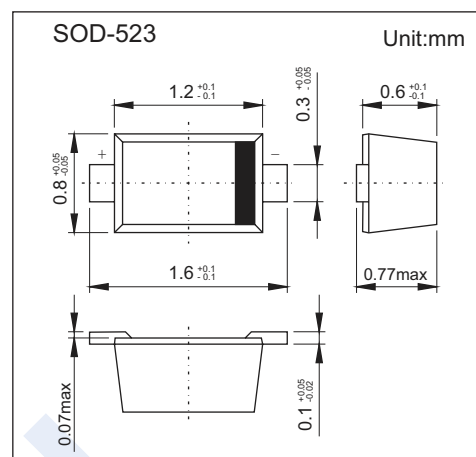


High Speed Switching Diode

1SS387

■ Features

- Small package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	85	V
DC Blocking Voltage	V_R	80	
Average Rectified Output Current	I_o	100	mA
Peak Forward Surge Current	I_{FM}	200	
Surge Current ($t=10\text{ms}$)	I_{surge}	1000	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	85			V
Forward voltage	V_{F1}	$I_F = 1 \text{ mA}$		0.62		
	V_{F2}	$I_F = 10 \text{ mA}$		0.75		
	V_{F3}	$I_F = 100 \text{ mA}$			1.2	
Reverse voltage leakage current	I_{R1}	$V_R = 30 \text{ V}$			0.1	μA
	I_{R2}	$V_R = 80 \text{ V}$			0.5	
Capacitance between terminals	C_T	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			3	pF
Reverse recovery time	t_{rr}	$V_R = 6 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$			4	ns

■ Marking

Marking	A1
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